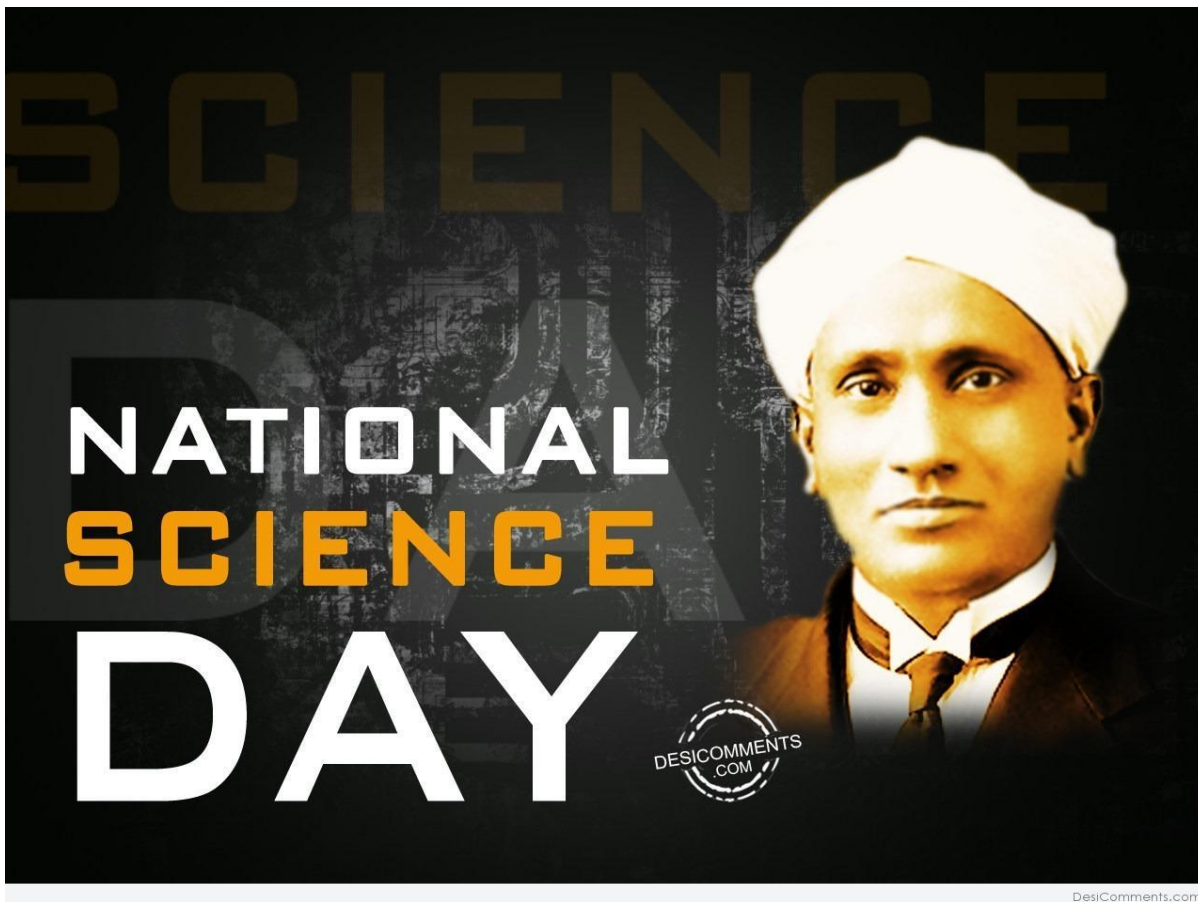


# XII STANDARD ENGLISH MEDIUM PHYSICS PRACTICAL MANUAL



Success can come to you by courageous devotion to the task lying in front of you.

- C.V.Raman

Practical manual prepared by  
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S.NO.	DATE	NAME OF THE EXPERIMENT	TEACHER'S INITIAL
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An experiment is a question which science poses to Nature, and a measurement is the recording of Nature's answer.

- Max Planck



Length of the coil  $L = \dots\dots\dots$  cm

Mean diameter  $2r = \dots\dots\dots$  mm      Radius of the wire  $r = \dots\dots\dots$  mm

$r = \dots\dots\dots$  m

### CALCULATION:

1.  $X = \frac{X_1 + X_2}{2} =$

2.  $X = \frac{X_1 + X_2}{2}$

3.  $X = \frac{X_1 + X_2}{2} =$

Mean  $X = \frac{X_1 + X_2}{2} =$

Specific resistance of the coil  $\rho = \frac{\pi r^2 X}{L} (\Omega \text{ m})$

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### PROCEDURE:

1. Circuit connections are made as shown in the diagram.
2. With a suitable resistance included in the resistance box, the circuit is switched on.
3. Jockey is moved on the wire. Balance point is noted where the galvanometer shows null deflection.
4.  $AJ = l$  is noted. The unknown resistance  $X_1 = \frac{R(100-l)}{l}$
5. The experiment is repeated for different values of R.
6. After interchanging R and X, the unknown resistance is found by  $X_2 = \frac{Rl}{(100-l)}$
7. Experiment is repeated. The mean value of  $X_1$  and  $X_2$  is found.
8. By using radius r and length L, the specific resistance of the material is determined by the

formula  $\rho = \frac{\pi r^2 X}{L}$

### RESULT:

The specific resistance of the material of the given coil =  $\dots\dots\dots$   $\Omega \text{ m}$

**EX. NO:      HORIZONTAL COMPONENT OF EARTH'S MAGNETIC      DATE:**  
**FIELD USING TANGENT GALVANOMETER**

**AIM: To determine the horizontal component of the Earth's magnetic field using tangent galvanometer.**

**FORMULA:**

$$B_H = \frac{\mu_0 n k}{2r} \text{ (tesla)} \qquad k = I / \tan \theta \text{ (A)}$$

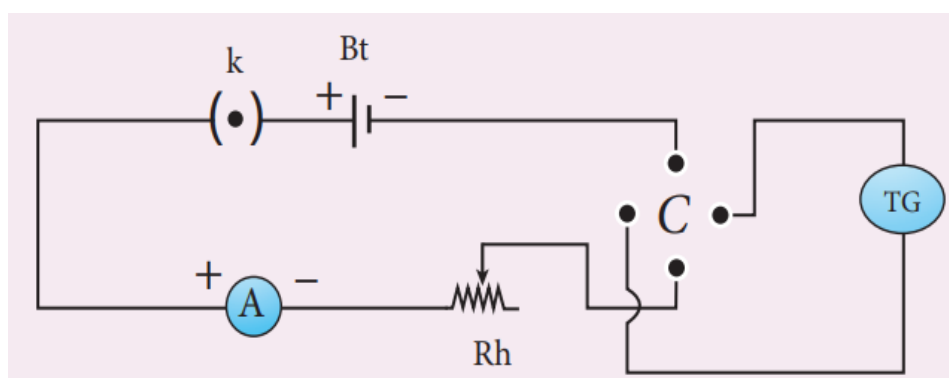
Where,  $B_H$  – Horizontal component of the Earth's magnetic field ( T )

$\mu_0$  – Permeability of free space (  $4 \pi \times 10^{-7} \text{ H m}^{-1}$  )

$n$  – Number of turns of TG in the circuit ( no unit )

$k$  – Reduction factor of TG ( A )       $r$  – Radius of the coil ( m )

**CIRCUIT DIAGRAM:**



Bt – Battery  
 K – Key  
 A – Ammeter  
 Rh – Rheostat  
 C – Commutator  
 TG – Tangent Galvanometer

**OBSERVATION:**

Number of turns of the coil =      Circumference of the coil (  $2 \pi r$  ) =

Radius of the coil  $r$  =

S.No.	Current I ( A )	Deflection in TG ( Degree )				Mean $\theta$	Tan $\theta$	$k = I / \tan \theta$
		$\theta_1$	$\theta_2$	$\theta_3$	$\theta_4$			
1								
2								
3								
4								

Mean

**CALCULATION:**

1)  $k = \frac{I}{\tan \theta} =$

2)  $k = \frac{I}{\tan \theta} =$

3)  $k = \frac{I}{\tan \theta} =$

4)  $k = \frac{I}{\tan \theta} =$

Mean  $k = \frac{I}{\tan \theta} =$

Horizontal component of Earth's magnetic field is  $B_H = \frac{\mu_0 n k}{2r}$

$B_H =$

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**PROCEDURE:**

1. Preliminary adjustments are carried out. Circuit connections are made.
2. A suitable current is allowed to pass through the circuit, the deflections  $\theta_1$ ,  $\theta_2$  are noted.
3. The direction of current is reversed using commutator C, the deflections  $\theta_3$ ,  $\theta_4$  are noted.  
Mean value  $\theta$  is found.
4. The reduction factor  $k = I / \tan \theta$  is found for each case and it is noted that  $k$  is a constant.
5. The experiment is repeated for various currents and the readings are noted and tabulated.
6. The radius of the circular coil is then found. By using the values of  $r$ ,  $n$  and  $k$  the value of horizontal component of earth's magnetic field is found by using the formula

$$B_H = \frac{\mu_0 n k}{2r} \text{ ( tesla )}$$

**RESULT:** The horizontal component of earth's magnetic is found to be = ..... T.

**EX. NO: VERIFICATION OF TRUTH TABLES OF LOGIC GATES DATE:**  
**USING INTEGRATED CIRCUITS**

**AIM: To verify the truth tables of AND, OR, NOT, EX-OR, NAND and NOR gates using IC's.**

**BOOLEAN EXPRESSIONS:**

(i) AND gate  $Y = A \cdot B$

(ii) OR gate  $Y = A + B$

(iii) NOT gate  $Y = \bar{A}$

(iv) EX - OR gate  $Y = A \oplus B = \bar{A}B + A\bar{B}$

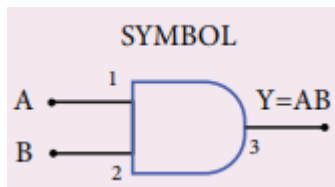
(v) NAND gate  $Y = \overline{A \cdot B}$

(vi) NOR gate  $Y = \overline{A + B}$

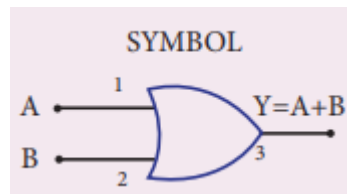
Where  $A$  and  $B$  are inputs.  $Y$  is the output.

**LOGIC SYMBOLS:**

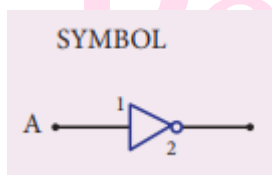
**1. AND Gate:**



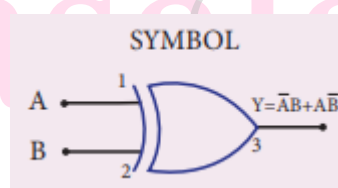
**2. OR Gate:**



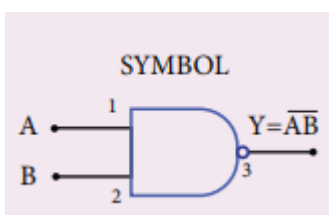
**3. NOT Gate:**



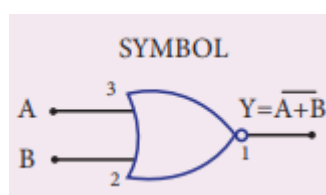
**4. EX-OR Gate:**



**5. NAND Gate:**



**6. NOR Gate:**



**TRUTH TABLES:**

**1. AND Gate:**

A	B	$Y = A \cdot B$
0	0	0
0	1	0
1	0	0
1	1	1

**2. OR Gate:**

A	B	$Y = A + B$
0	0	0
0	1	1
1	0	1
1	1	1

**3. NOT Gate:**

A	$Y = \bar{A}$
0	1
1	0

**4. EX – OR Gate:**

A	B	$Y = \bar{A} B + A \bar{B}$
0	0	0
0	1	1
1	0	1
1	1	0

**5. NAND Gate:**

A	B	$Y = \overline{A \cdot B}$
0	0	1
0	1	1
1	0	1
1	1	0

**6. NOR Gate:**

A	B	$Y = \overline{A + B}$
0	0	1
0	1	0
1	0	0
1	1	0

**CALCULATION:****1. AND Gate:**

A	B	$Y = A \cdot B$
0	0	$Y = 0 \cdot 0 = 0$
0	1	
1	0	
1	1	

**2. OR Gate:**

A	B	$Y = A + B$
0	0	$Y = 0 + 0 = 0$
0	1	
1	0	
1	1	

**3. NOT Gate:**

A	$Y = \bar{A}$
0	$Y = \bar{0} = 1$
1	

**4. EX-OR Gate:**

A	B	$Y = \bar{A} B + A \bar{B}$
0	0	$Y = \bar{0} \cdot 0 + 0 \cdot \bar{0} = 0$
0	1	
1	0	
1	1	

**5. NAND Gate:**

A	B	$Y = \overline{A \cdot B}$
0	0	$Y = \overline{0 \cdot 0} = 1$
0	1	
1	0	
1	1	

**6. NOR Gate:**

A	B	$Y = \overline{A + B}$
0	0	$Y = \overline{0 + 0} = 1$
0	1	
1	0	
1	1	

**PROCEDURE:**

1. To verify the truth table of a logic gate, the suitable IC is taken and the connections are given.
2. For all the ICs, 5 V is applied to pin 14 while the pin 7 is connected to the ground.
3. The logical inputs of the truth table are applied and the corresponding output is noted.
4. Similarly the output is noted for all other combinations of inputs.
5. In this way, the truth table of a logic gate is verified.

**RESULT:** The truth table of logic gates OR, AND, NOT, EX-OR, NOR and NAND gates using integrated circuits is verified.



EX.NO: VOLTAGE – CURRENT CHARACTERISTICS OF A

DATE:

**PN JUNCTION DIODE**

**AIM:** To draw the V- I characteristics of the PN junction diode and to determine its knee voltage and forward resistance.

**FORMULA:**

$$R_F = \frac{\Delta V_F}{\Delta I_F} (\Omega)$$

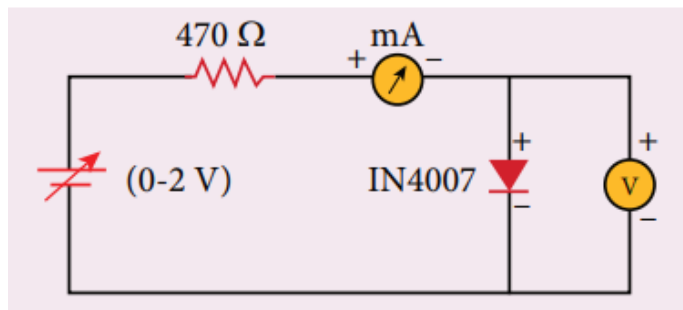
where,  $R_F$  – Forward resistance of the diode ( $\Omega$ )

$\Delta V_F$  - The change in forward voltage ( volt )

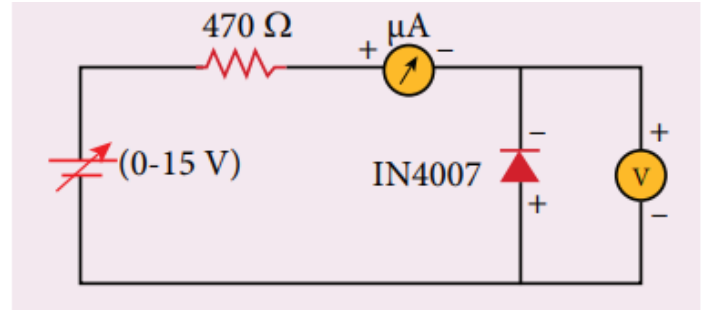
$\Delta I_F$  - The change in forward current ( m A )

**CIRCUIT DIAGRAM:**

**FORWARD BIAS**



**REVERSE BIAS**



**OBSERVATION:**

**FORWARD BIAS CHARACTERISTIC CURVE**

**REVERSE BIAS CHARACTERISTIC CURVE**

S.No.	Forward bias voltage $V_F$ ( volt )	Forward bias current $I_F$ ( m A )	S.No.	Reverse bias voltage $V_R$ ( volt )	Reverse bias current $I_R$ ( $\mu$ A )
1			1		
2			2		
3			3		
4			4		
5			5		
6			6		
7			7		
8			8		

**CALCULATION:**

Forward resistance of the PN junction diode is

$$R_F = \frac{\Delta V_F}{\Delta I_F} =$$

Knee voltage of the P-N junction diode =

**PROCEDURE:****FORWARD BIAS:**

1. The connections are made as in the circuit.
2. The voltage across the diode can be varied with the help of variable DC power supply.
3. The forward voltage ( $V_F$ ) is increased from 0.1 V to 0.8 V in suitable equal steps.
4. The corresponding current ( $I_F$ ) is noted from milli ammeter.  $V_F$  and  $I_F$  are positive.
5. A graph is drawn by taking  $V_F$  along X-axis and  $I_F$  along Y-axis.
6. From the forward characteristic curve, knee voltage is marked and noted. The reciprocal of the slope gives the forward resistance of the diode.

**REVERSE BIAS**

1. The connections are made as in the circuit.
2. The voltage across the diode can be varied with the help of variable DC power supply.
3. The reverse voltage ( $V_R$ ) across the diode is increased from 1 V in steps of 1 V upto V
4. The corresponding current  $I_R$  is noted from the micro ammeter.  $V_R$  and  $I_R$  are negative.
5. A graph is drawn by taking  $V_R$  along negative X-axis and  $I_R$  along negative Y-axis.

**RESULT:**

The V – I characteristics of the PN junction diode are studied.

- i) Knee Voltage of the PN junction diode = ..... V
- ii) Forward resistance of the diode = .....  $\Omega$

**NOTE:** In the circuit diagram, the diode should be named as 1 N 4007 instead of IN 4007.

EX.NO.

REFRACTIVE INDEX OF THE MATERIAL

DATE:

OF THE PRISM

AIM:

To determine the refractive index of the material of a prism using spectrometer.

FORMULA:

$$\mu = \frac{\sin\left(\frac{A+D}{2}\right)}{\sin\left(\frac{A}{2}\right)}$$

where,  $\mu$  – Refractive index of the material of the prism ( No unit )

A - Angle of the prism ( degree )

D – Angle of minimum deviation ( degree )

OBSERVATION:

TABLE 1: To find the angle of the prism ( A )

Image	Vernier A ( Degree )			Vernier B ( Degree )		
	MSR	VSC	TR	MSR	VSC	TR
Reflected Image from face 1						
Reflected Image from face 2						
Difference 2A						

Mean 2 A =

Mean A =

PROCEDURE:

1. Initial adjustments are made.
2. The slit is illuminated by sodium vapour lamp.
3. Prism is placed on the prism table with its refracting edge facing the collimator.
4. Light is getting reflected from both reflecting faces of the prism.
5. The telescope is rotated to left to obtain reflected image of the slit. Vernier A and B readings are noted.
6. Telescope is then rotated to right to obtain the other reflected image of the slit. Vernier readings are noted.
7. The difference between the two readings gives 2A from which the angle of the prism A is calculated.

**CALCULATION: To find the value of A:**

**TABLE 2: To find the angle of minimum deviation ( D )**

Image	Vernier A ( Degree )			Vernier B ( Degree )		
	MSR	VSC	TR	MSR	VSC	TR
Refracted image						
Direct image						
Difference D						

Mean D =

**PROCEDURE:**

1. Prism is placed on the prism table so that light is incident on one of the refracting faces.
2. Telescope is turned to view the refracted image.
3. Keeping the telescope fixed, prism table is rotated so that the image moves towards the direct ray.
4. At a particular position, the refracted ray begins to retrace its path. – POSITION OF MINIMUM DEVIATION.
5. Vertical cross wires are made to coincide with the ray. Vernier readings are noted.
6. After removing the prism, direct ray is made to coincide with the vertical cross wires. Direct ray readings are noted.
7. Difference between the two readings gives the angle of minimum deviation D. From the values of A and D, the refractive index of the material of the prism is determined.

**CALCULATION: To find the value of D:**

**CALCULATION: To find the value of  $\mu$ :**

NSR  
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**RESULT:**

1. Angle of the prism ( A ) = ..... degree
2. Angle of minimum deviation of the prism ( D ) ..... degree
3. Refractive index of the material of the prism (  $\mu$  ) = ..... ( no unit )

EX.NO: VOLTAGE-CURRENT CHARACTERISTICS OF A

DATE:

**ZENER DIODE**

**AIM:** To draw the V-I characteristic curves of a Zener diode and to determine its knee voltage, forward resistance and reverse breakdown voltage.

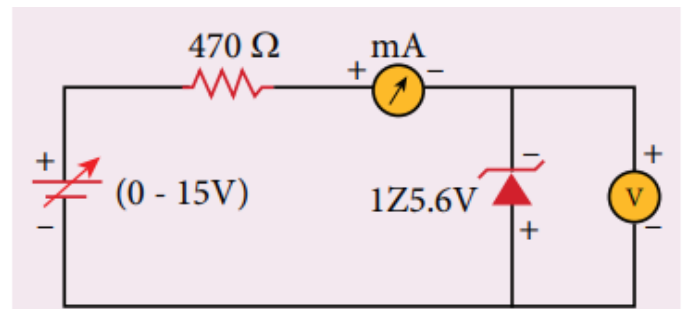
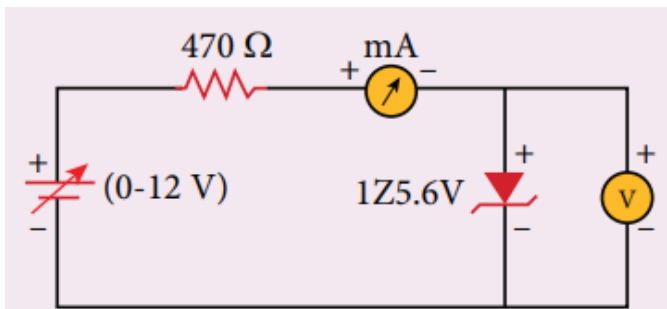
**FORMULA:**

$$R_F = \frac{\Delta V_F}{\Delta I_F} \Omega$$

where,  $R_F$  - Forward resistance of the diode (  $\Omega$  )

$\Delta V_F$  - Change in forward voltage ( volt )

$\Delta I_F$  - Change in forward current ( m A )

**CIRCUIT DIAGRAM:****OBSERVATION****FORWARD BIAS CHARACTERISTICS****REVERSE BIAS CHARACTERISTICS**

S.NO.	Forward bias voltage $V_F$ ( V )	Forward bias current $I_F$ ( mA )	S.NO.	Reverse bias voltage $V_R$ ( V )	Reverse bias current $I_R$ ( mA )
1			1		
2			2		
3			3		
4			4		
5			5		
6			6		

**CALCULATION:**

Forward resistance of the diode  $R_F = \frac{\Delta V_F}{\Delta I_F}$

Knee voltage = ..... volt

Breakdown voltage of the Zener diode  $V_Z = \dots\dots\dots$  Volt

**PROCEDURE:****FORWARD BIAS CHARACTERISTICS**

1. The connections are given as per the circuit.
2. The voltage can be varied with the help of variable DC power supply.
3.  $V_F$  is increased from 0.1 V upto 0.6 V and the corresponding current  $I_F$  is noted.
4.  $V_F$  and  $I_F$  are taken as positive.
5.  $V_F$  is taken along X-axis and  $I_F$  is taken along Y-axis.
6. The voltage corresponding to the dotted line gives knee voltage. A slope is drawn and the reciprocal of the slope gives  $R_F$ .

**REVERSE BIAS CHARACTERISTICS**

1. The connections are given as per the circuit.
2. The voltage can be varied with the help of variable DC power supply.
3.  $V_R$  is increased from 1 V upto 6 V and the corresponding current  $I_R$  is noted.
4.  $V_R$  and  $I_R$  are taken as negative.
5.  $V_R$  is taken along negative X-axis and  $I_R$  is taken along negative Y-axis.
6. Zener breakdown occurs at a particular voltage. It is determined from the graph drawn.

**RESULT:**

i) Forward resistance  $R_F = \dots\dots\dots \Omega$

ii) Knee voltage = ..... volt

iii) Breakdown voltage of the Zener diode  $V_Z = \dots\dots\dots$  volt

**EX.NO: CHARACTERISTICS OF A NPN-JUNCTION TRANSISTOR IN COMMON EMITTER CONFIGURATION DATE:**

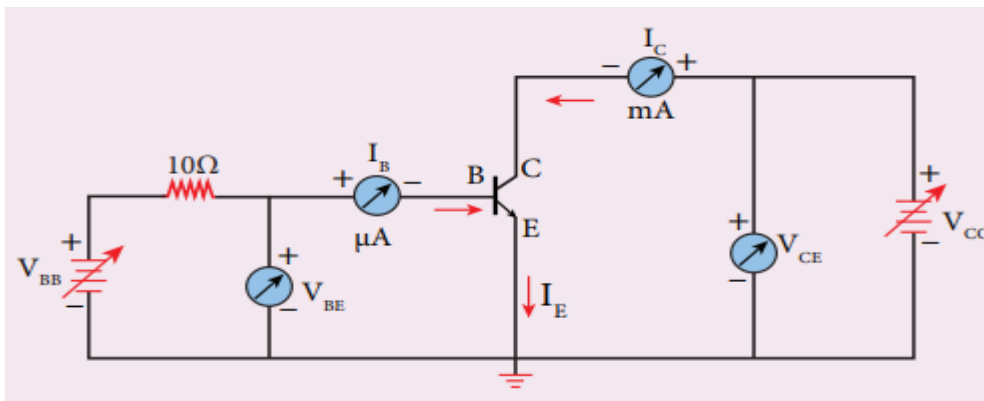
**AIM: To study the input characteristics and to determine the current gain of a NPN junction transistor in CE configuration.**

**FORMULA:**

$$\text{Input impedance } r_i = \left[ \frac{\Delta V_{BE}}{\Delta I_B} \right] V_{CE} \quad \Omega$$

$$\text{Current gain } \beta = \left[ \frac{\Delta I_C}{\Delta I_B} \right] V_{CE} \quad (\text{No unit})$$

**CIRCUIT DIAGRAM:**



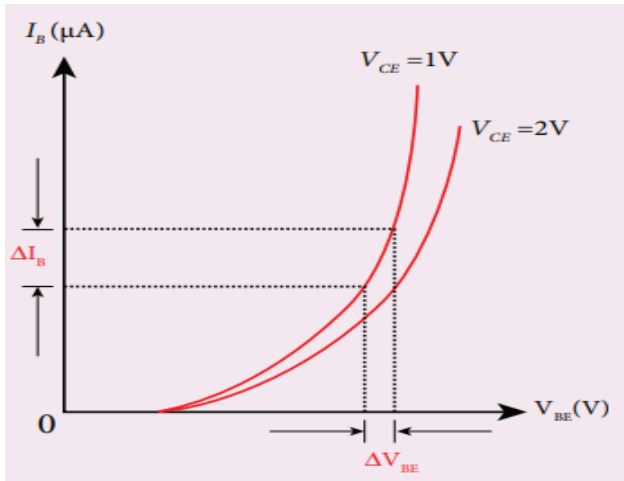
**OBSERVATION:**

**TABLE 1: INPUT CHARACTERISTIC CURVE:  $V_{BE}$  vs  $I_B$  ( $V_{CE}$  constant)**

S.NO.	$V_{CE} = 1 \text{ V}$		$V_{CE} = 2 \text{ V}$	
	$V_{BE} \text{ (V)}$	$I_B \text{ (}\mu\text{A)}$	$V_{BE} \text{ (V)}$	$I_B \text{ (}\mu\text{A)}$
1				
2				
3				
4				
5				
6				
7				
8				
9				
10				



**CALCULATION:**

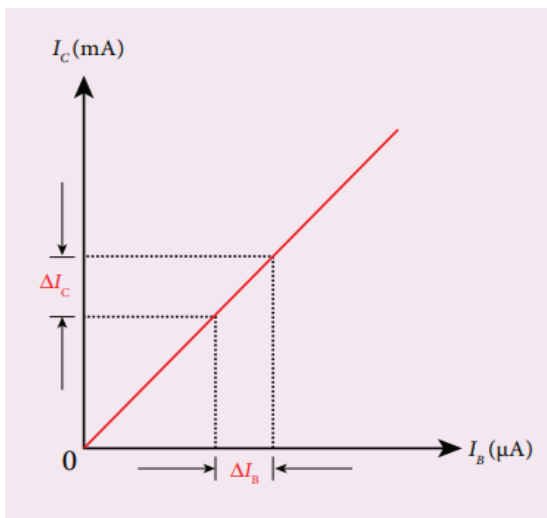


$$\text{Slope} = \frac{\Delta I_B}{\Delta V_{BE}}$$

$$\text{Input impedance} = \frac{1}{\text{slope}} = \left[ \frac{\Delta V_{BE}}{\Delta I_B} \right]$$

**TABLE 2: TRANSFER CHARACTERISTIC CURVE: IB vs IC ( VCE constant )**

S.No.	V <sub>CE</sub> = 1 V		V <sub>CE</sub> = 2 V	
	I <sub>B</sub> ( µ A )	I <sub>C</sub> ( m A )	I <sub>B</sub> ( µ A )	I <sub>C</sub> ( m A )
1				
2				
3				
4				
5				
6				
7				



**CALCULATION:**

$$\text{Slope} = \frac{\Delta I_C}{\Delta I_B}$$

**Current gain = slope**

**PROCEDURE:****INPUT CHARACTERISTICS:**

1.  $V_{CE}$  is kept constant.
2.  $V_{BE}$  is varied in steps of 0.1 V and the corresponding  $I_B$  is noted.
3. The same procedure is repeated for different values of  $V_{CE}$ .
4.  $V_{BE}$  is taken along X-axis and  $I_B$  is taken along Y-axis.
5. The curves obtained are called the input characteristics.
6. The reciprocal of the slope of these curves gives input impedance of the transistor.

**TRANSFER CHARACTERISTICS:**

1.  $V_{CE}$  is kept constant.
2.  $I_B$  is varied in steps of 10  $\mu A$  and the corresponding  $I_C$  is noted.
3. The readings are tabulated.
4.  $I_B$  is taken along X-axis and  $I_C$  is taken along Y-axis.
5. The slope of the characteristic curve gives current gain  $\beta$ .

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**RESULT:**

i ) The input and transfer characteristics of the NPN junction in CE mode are drawn.

- ii) a) Input impedance = .....  $\Omega$   
b) Current gain  $\beta$  = ..... ( no unit )

**EX.NO: CHARACTERISTICS OF A NPN-JUNCTION TRANSISTOR DATE:**  
**IN COMMON EMITTER CONFIGURATION**

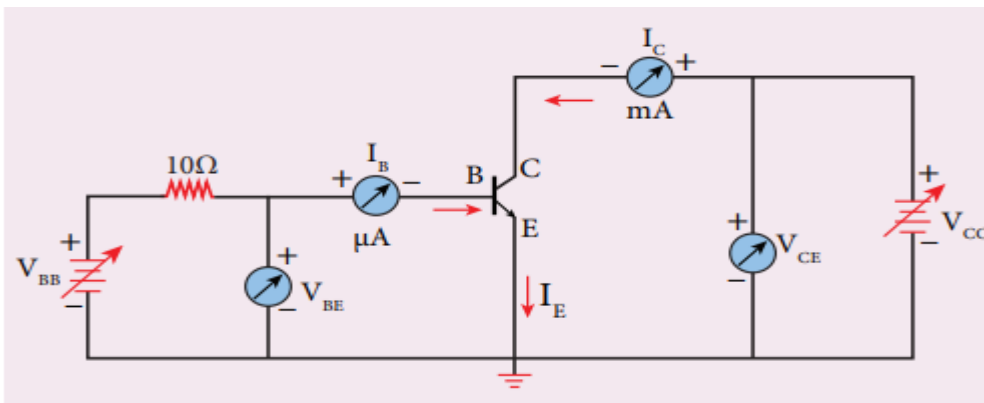
**AIM: To study the output characteristics and to determine the current gain of a NPN junction transistor in CE configuration.**

**FORMULA:**

$$\text{Output impedance } r_o = \left[ \frac{\Delta V_{CE}}{\Delta I_C} \right] I_B \quad \Omega$$

$$\text{Current gain } \beta = \left[ \frac{\Delta I_C}{\Delta I_B} \right] V_{CE} \quad (\text{No unit})$$

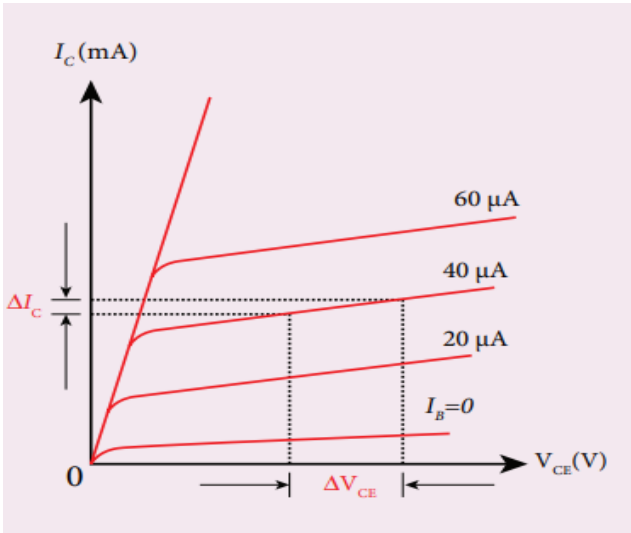
**CIRCUIT DIAGRAM:**



**OBSERVATION:**

**TABLE 1: OUTPUT CHARACTERISTIC CURVE:  $V_{BE}$  vs  $I_B$  ( $V_{CE}$  constant)**

S.NO.	$I_B = 20 \mu\text{A}$		$I_B = 40 \mu\text{A}$	
	$V_{CE}$ (V)	$I_C$ (mA)	$V_{CE}$ (V)	$I_C$ (mA)
1				
2				
3				
4				
5				
6				
7				
8				
9				
10				



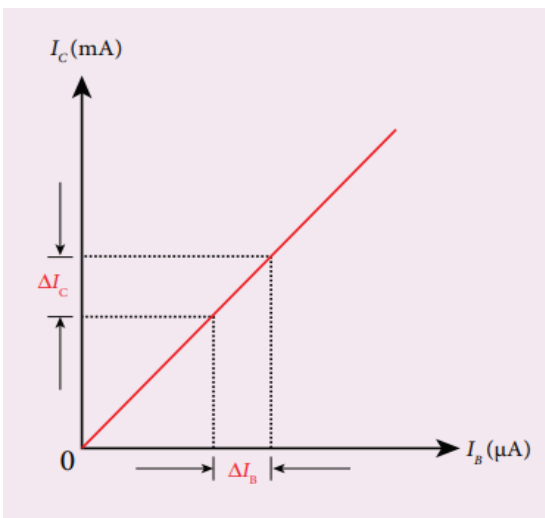
**CALCULATION:**

$$\text{Slope} = \frac{\Delta I_C}{\Delta V_{CE}}$$

$$\text{Output impedance} = \frac{1}{\text{slope}} = \left[ \frac{\Delta V_{CE}}{\Delta I_C} \right]$$

**TABLE 2: TRANSFER CHARACTERISTIC CURVE: IB vs IC ( VCE constant )**

S.No.	V <sub>CE</sub> = 1 V		V <sub>CE</sub> = 2 V	
	I <sub>B</sub> ( μ A )	I <sub>C</sub> ( m A )	I <sub>B</sub> ( μ A )	I <sub>C</sub> ( m A )
1				
2				
3				
4				
5				
6				
7				



**CALCULATION:**

$$\text{Slope} = \frac{\Delta I_C}{\Delta I_B}$$

**Current gain = slope**

**PROCEDURE:****OUTPUT CHARACTERISTICS:**

1.  $I_B$  is kept constant.
2.  $V_{CE}$  is varied in steps of 1 V and the corresponding  $I_C$  is noted.
3. The same procedure is repeated for different values of  $I_B$ .
4.  $V_{CE}$  is taken along X-axis and  $I_C$  is taken along Y-axis.
5. The curves obtained are called the output characteristics.
6. The reciprocal of the slope of these curves gives output impedance of the transistor.

**NOTE:** The collector current which is noted at  $I_B$  is at zero is called

**REVERSE SATURATION CURRENT  $I_{CRO}$**

**TRANSFER CHARACTERISTICS:**

1.  $V_{CE}$  is kept constant.
2.  $I_B$  is varied in steps of 10  $\mu A$  and the corresponding  $I_C$  is noted.
3. The readings are tabulated.
4.  $I_B$  is taken along X-axis and  $I_C$  is taken along Y-axis.
5. The slope of the characteristic curve gives current gain  $\beta$ .

**RESULT:**

- i) The input and transfer characteristics of the NPN junction in CE mode are drawn.
- ii) a) Input impedance = .....  $\Omega$   
 b) Current gain  $\beta$  = ..... ( no unit )

**EX. NO:                      COMPARISON OF EMF OF TWO CELLS USING  
POTENTIOMETER**

**DATE:**

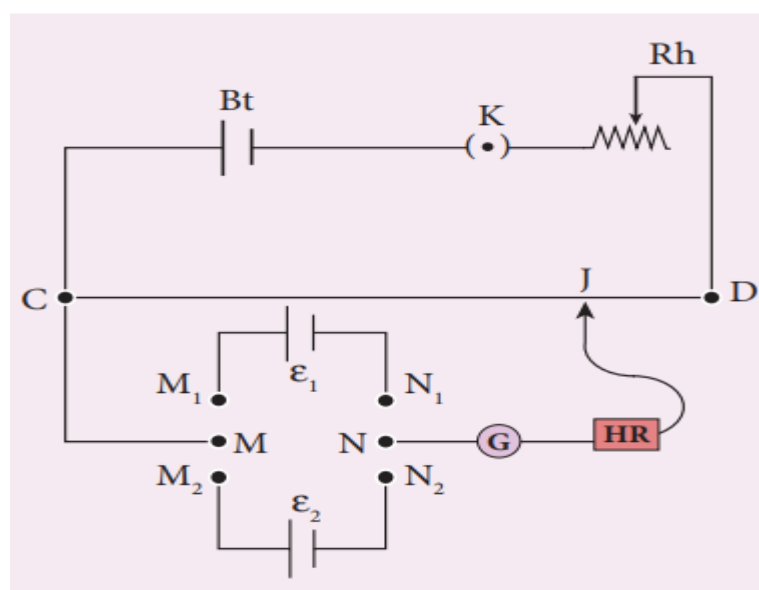
**AIM:** To compare the emf of the given two cells using a potentiometer.

**FORMULA:**  $\frac{\epsilon_1}{\epsilon_2} = \frac{l_1}{l_2}$  (no unit)

where,  $\epsilon_1$  and  $\epsilon_2$  are the emf of Lechlanche and Daniel cells respectively ( V )

$l_1$  and  $l_2$  are the balancing lengths for Lechlanche and Daniel cells respectively ( cm )

**CIRCUIT DIAGRAM:**



**Bt - Battery**

**K - Key**

**Rh - Rheostat**

**C D - Potentiometer wire**

**M<sub>1</sub> M<sub>2</sub> N<sub>1</sub> N<sub>2</sub> - DPDT switch**

**G - Galvanometer**

**HR - High Resistance**

**J - Jockey**

**OBSERVATION:**

S. No.	Balancing length for Lechlanche cell $l_1$ ( cm )	Balancing length for Daniel cell $l_2$ ( cm )	$\frac{\epsilon_1}{\epsilon_2} = \frac{l_1}{l_2}$
1.			
2.			
3.			
4.			
5.			
6.			

Mean  $\frac{\epsilon_1}{\epsilon_2} =$

**CALCULATION:**

1.  $\frac{\varepsilon_1}{\varepsilon_2} = \frac{l_1}{l_2} =$

2.  $\frac{\varepsilon_1}{\varepsilon_2} = \frac{l_1}{l_2} =$

3.  $\frac{\varepsilon_1}{\varepsilon_2} = \frac{l_1}{l_2} =$

4.  $\frac{\varepsilon_1}{\varepsilon_2} = \frac{l_1}{l_2} =$

5.  $\frac{\varepsilon_1}{\varepsilon_2} = \frac{l_1}{l_2} =$

6.  $\frac{\varepsilon_1}{\varepsilon_2} = \frac{l_1}{l_2} =$

Mean  $\frac{\varepsilon_1}{\varepsilon_2} =$

**PROCEDURE:**

1. The circuit connections are made as shown in the diagram.
2. Primary circuit: Potentiometer wire is connected to a battery, key and rheostat in series.
3. Secondary circuit: The positive poles of the cells are connected to terminals  $M_1$  and  $M_2$  and the negative poles to terminals  $N_1$  and  $N_2$  of the DPDT switch.
4. The potentiometer is connected to the common terminals M and N as shown in the circuit.
5. Using the two way key, Lechlanche cells is included in the circuit. By sliding the jockey on the potentiometer wire, the balancing length is found and the corresponding balancing length is measured.
6. Similarly, the balancing length is found by including Daniel cell in the circuit.
7. The experiment is repeated for different sets of balancing lengths by adjusting the rheostat.
8. From different values of  $l_1$  and  $l_2$ , the ratio of emf of the two cells is calculated using the

formula  $\frac{\varepsilon_1}{\varepsilon_2} = \frac{l_1}{l_2}$ .

**RESULT:** Ratio of emf of the given two cells is = ..... ( no unit )

EX.NO:

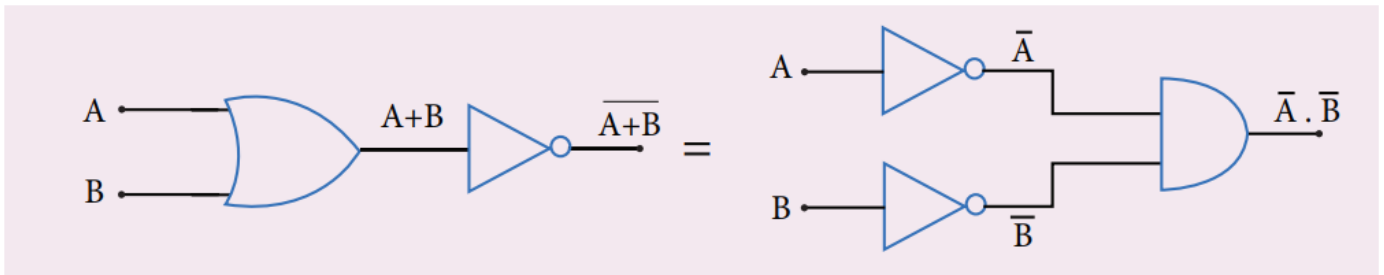
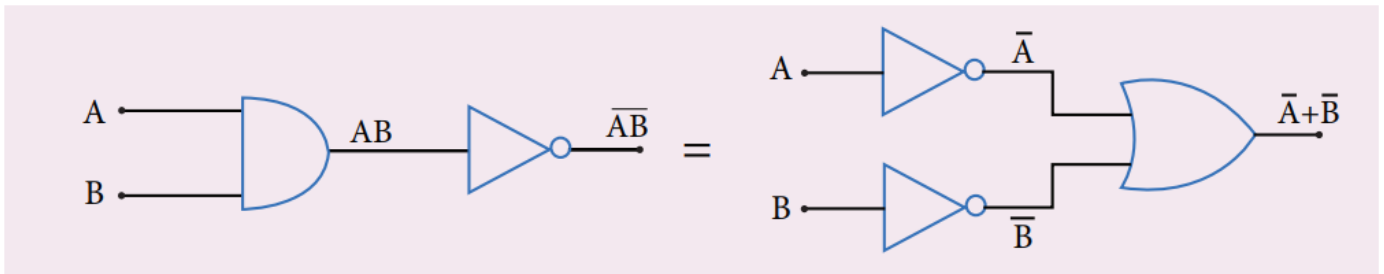
VERIFICATION OF DE MORGAN'S THEOREMS

DATE:

AIM: To verify De Morgan's first and second theorems.

FORMULA: De Morgan's theorems: Theorem I:  $\overline{A + B} = \bar{A} \cdot \bar{B}$ Theorem II:  $\overline{A \cdot B} = \bar{A} + \bar{B}$ 

CIRCUIT DIAGRAM:

**De Morgan's first theorem****De Morgan's second theorem**

OBSERVATION:

De Morgan's first theorem: TRUTH TABLE

A	B	$\overline{A + B}$	$\bar{A} \cdot \bar{B}$
0	0		
0	1		
1	0		
1	1		



## De Morgan's second theorem: TRUTH TABLE

A	B	$\overline{A \cdot B}$	$\overline{A} + \overline{B}$
0	0		
0	1		
1	0		
1	1		

## CALCULATION:

Theorem I:	A	B	$\overline{A + B}$	A	B	$\overline{A} \cdot \overline{B}$
	0	0	$\overline{0 + 0} = \overline{0} = 1$	0	0	$\overline{0} \cdot \overline{0} = \overline{0} = 1$
	0	1				
	1	0				
	1	1				

Calculation: Theorem II:	A	B	$\overline{A \cdot B}$	A	B	$\overline{A} + \overline{B}$
	0	0	$\overline{0 \cdot 0} = \overline{0} = 1$	0	0	$\overline{0} + \overline{0} = \overline{0} = 1$
	0	1				
	1	0				
	1	1				

## PROCEDURE:

## Theorem I:

- The connections are made for LHS ( $\overline{A + B}$ ) using appropriate IC's.
- The output is noted and tabulated for all combinations of logical inputs of the truth table.
- The same procedure is repeated for RHS ( $\overline{A} \cdot \overline{B}$ ) of the theorem.
- From the truth table, it can be shown that

$$\overline{A + B} = \overline{A} \cdot \overline{B}$$

## Theorem II:

- The connections are made for LHS ( $\overline{A \cdot B}$ ) using appropriate IC's.
- The output is noted and tabulated for all combinations of logical inputs of the truth table.
- The same procedure is repeated for RHS ( $\overline{A} + \overline{B}$ ) of the theorem.
- From the truth table it can be shown that

$$\overline{A \cdot B} = \overline{A} + \overline{B}$$

RESULT: De Morgan's first and second theorems are verified.

**EX.NO:    WAVELENGTH OF THE CONSTITUENT COLOURS OF A        DATE:**  
**LIGHT USING DIFFRACTION GRATING AND**  
**SPECTROMETER**

**AIM: To find the wavelength of the constituent colours of a composite light using diffraction grating and spectrometer.**

**FORMULA:**

$$\lambda = \frac{\sin \theta}{nN} \quad \text{\AA}$$

where,  $\lambda$  – Wavelength of the constituent colours of a composite light (  $\text{\AA}$  )

$N$  – Number of lines per metre length of the grating ( no unit ) ( Given )

$n$  – Order of diffraction ( no unit )

$\theta$  – Angle of diffraction ( degree )

**PROCEDURE:**

1. Initial adjustments are made. The slit of the spectrometer is illuminated by mercury vapour lamp.
2. The telescope is brought in line with the collimator. Undispersed white image is obtained.
3. The vernier disc alone is rotated till the vernier scale reads  $0^{\circ} - 180^{\circ}$  and is fixed. This is the reading for direct ray.
4. The diffraction grating is placed on the table.
5. On either side of the direct image, diffracted images of the slit are observed.
6. The telescope is turned to left side to observe first order diffracted image.
7. The vertical cross wire is made to coincide with the colours blue, green, yellow and red. Readings both vernier scales are noted.
8. Similarly, on the right side the same procedure is repeated and the vernier readings are noted.
9. The difference between these two readings gives the value of  $2\theta$  from which  $\theta$  is calculated.
10. From the values of  $N$ ,  $n$  and  $\theta$ , the wavelength of the prominent colours of the mercury spectrum are found using the formula given.

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**CALCULATION:**

( i ) **BLUE :**  $\lambda = \frac{\sin \theta}{n N}$

( ii ) **GREEN:**  $\lambda = \frac{\sin \theta}{n N}$

( iii ) **YELLOW:**  $\lambda = \frac{\sin \theta}{n N}$

( iv ) **RED:**  $\lambda = \frac{\sin \theta}{n N}$

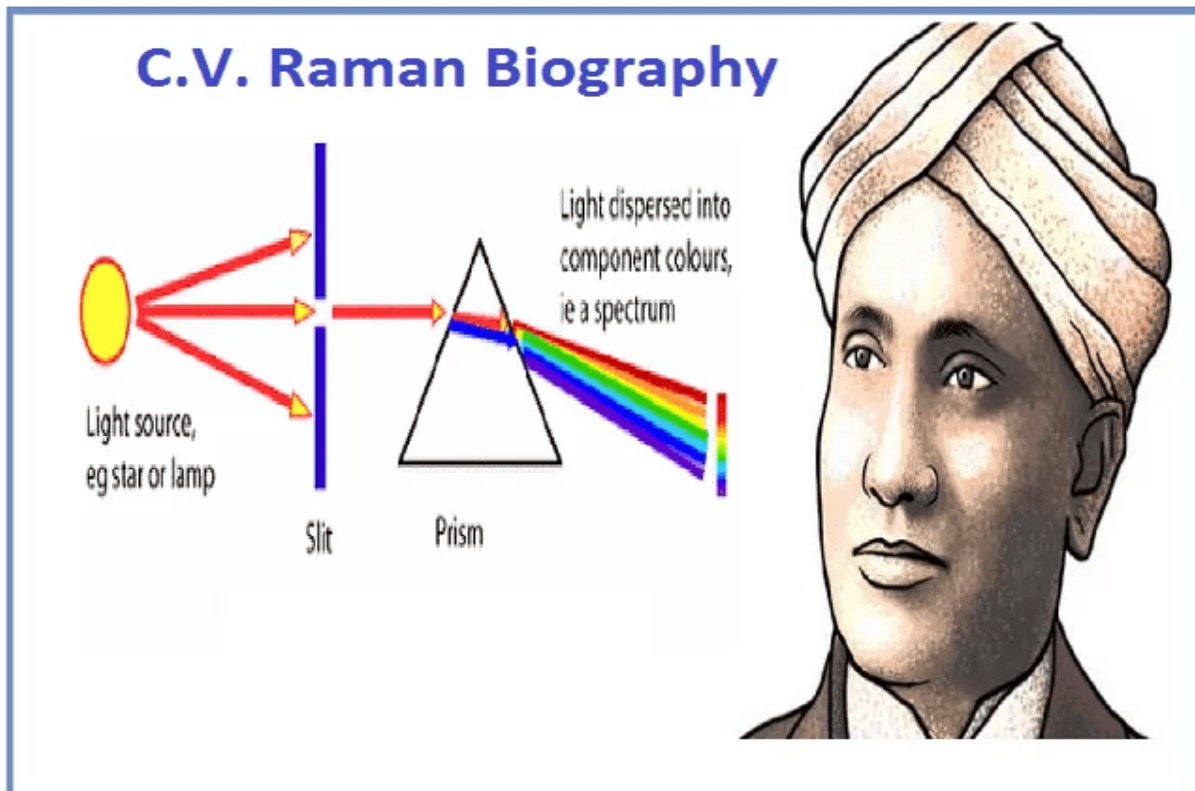
**RESULT:**

( i ) The wavelength of blue line = ..... Å

( ii ) The wavelength of green line = ..... Å

( iii ) The wavelength of yellow line = ..... Å

( iv ) The wavelength of red line = ..... Å



### Important Contributions of RAMAN

- Blue Colour of the Sea Water (1921)
- Discovery of RAMAN Effect (1928)
- Raman-Nath Theory (1934-1936)
- Studies on Brillouin Scattering (1933-40)
- Discovery of the Soft Mode (1938-40)
- Other contributions: Optical & Magnetic anisotropy, Acoustics & Indian Classical Music, Crystal Dynamics, Physiology of Colour and Vision.

et

THE REAL GROWTH OF A COUNTRY IS IN THE HEARTS, MINDS, BODIES AND SOULS OF YOUNG MEN AND WOMEN OF THE COUNTRY.

- C.V.Raman